1-Mbit (64K x 16) Static RAM

Features

- High speed: 45 ns
- Temperature ranges
  - — Industrial: –40°C to +85°C
  - — Automotive: –40°C to +125°C
- Wide voltage range: 2.2V–3.6V
- Pin compatible with CY62126DV30
- Ultra low standby power
  - — Typical standby current: 1 μA
  - — Maximum standby current: 4 μA
- Ultra low active power
  - — Typical active current: 1.3 mA @ f = 1 MHz
- Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features
- Automatic power down when deselected
- CMOS for optimum speed and power
- Offered in Pb-free 48-ball VFBGA and 44-pin TSOP II packages

Functional Description[1]

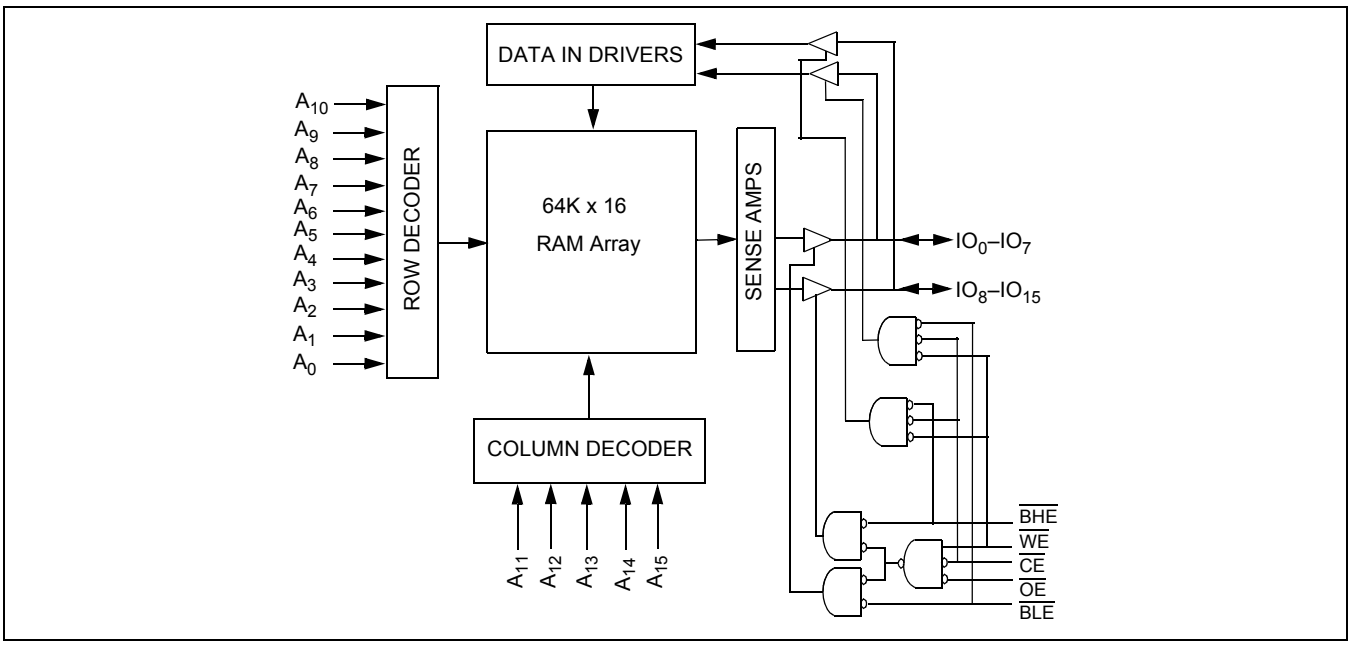
The CY62126EV30 is a high performance CMOS static RAM organized as 64K words by 16 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{CE}$ HIGH). The input and output pins (IO_0 through IO_{15}) are placed in a high impedance state when:

- Deselected ($\overline{CE}$ HIGH)
- Outputs are disabled ($\overline{OE}$ HIGH)
- Both Byte High Enable and Byte Low Enable are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH)
- Write operation is active ($\overline{CE}$ LOW and $\overline{WE}$ LOW)

To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from IO pins (IO_0 through IO_7) is written into the location specified on the address pins (A_0 through A_{15}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from IO pins (IO_8 through IO_{15}) is written into the location specified on the address pins (A_0 through A_{15}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins appear on IO_0 to IO_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory appears on IO_8 to IO_{15}. See the "Truth Table" on page 9 for a complete description of read and write modes.

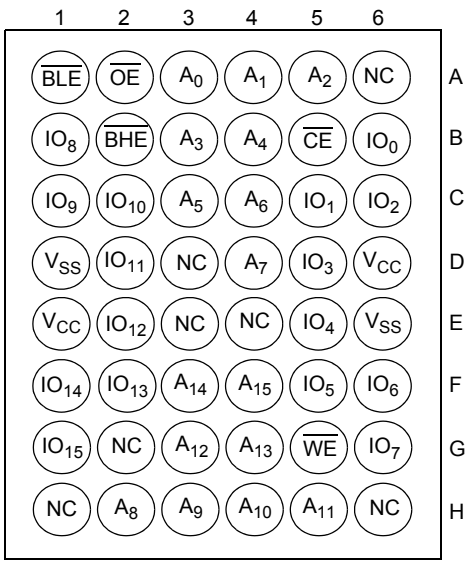
Logic Block Diagram



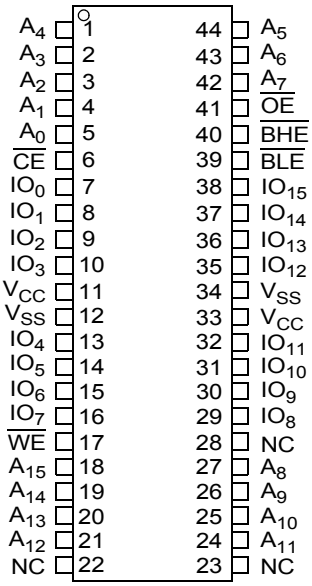
Note
1. For best practice recommendations, refer to the Cypress application note AN1064, SRAM System Guidelines.

Pin Configurations [2]

48-Ball VFBGA
Top View



44-Pin TSOP II
Top View



Product Portfolio

Product	Range	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
						Operating, I_{CC} (mA)				Standby, I_{SB2} (µA)	
						f = 1 MHz		f = f_{max}			
		Min	Typ[1]	Max		Typ[1]	Max	Typ[1]	Max	Typ[1]	Max
CY62126EV30LL	Industrial	2.2	3.0	3.6	45	1.3	2	11	16	1	4
CY62126EV30LL	Automotive	2.2	3.0	3.6	55	1.3	4	11	35	1	30

Notes
2. NC pins are not connected on the die.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25°C$.

Maximum Ratings

Exceeding maximum ratings may shorten the battery life of the device. These user guidelines are not tested.

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential.....–0.3V to 3.6V (V_{CCmax} + 0.3V)

DC Voltage Applied to Outputs in High-Z State[4, 5].....–0.3V to 3.6V (V_{CCmax} + 0.3V)

DC Input Voltage[4, 5].....–0.3V to 3.6V (V_{CCmax} + 0.3V)

Output Current into Outputs (LOW).....20 mA

Static Discharge Voltage..... > 2001V (MIL-STD-883, Method 3015)

Latch up Current..... > 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC}[6]
CY62126EV30LL	Industrial	–40°C to +85°C	2.2V to 3.6V
	Automotive	–40°C to +125°C	

Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		45 ns (Industrial)			55 ns (Automotive)			Unit
				Min	Typ[1]	Max	Min	Typ[1]	Max	
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA		2.0			2.0			V
		I_{OH} = –1.0 mA, $V_{CC} \geq$ 2.70V		2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA				0.4			0.4	V
		I_{OL} = 2.1mA, $V_{CC} \geq$ 2.70V				0.4			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC} = 2.2V to 2.7V		1.8		V_{CC} + 0.3	1.8		V_{CC} + 0.3	V
		V_{CC} = 2.7V to 3.6V		2.2		V_{CC} + 0.3	2.2		V_{CC} + 0.3	V
V_{IL}	Input LOW Voltage	V_{CC} = 2.2V to 2.7V		–0.3		0.6	–0.3		0.6	V
		V_{CC} = 2.7V to 3.6V		–0.3		0.8	–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–4		+4	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–4		+4	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{max} = $1/t_{RC}$	V_{CC} = V_{CCmax} I_{OUT} = 0 mA CMOS levels		11	16		11	35	mA
		f = 1 MHz			1.3	2.0		1.3	4.0	
I_{SB1}	Automatic CE Power down Current —CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, $V_{IN} \leq 0.2V$) f = f_{max} (Address and Data Only), f = 0 ($\overline{OE}$, $\overline{BHE}$, $\overline{BLE}$ and $\overline{WE}$), V_{CC} = 3.60V			1	4		1	35	µA
I_{SB2} [7]	Automatic CE Power down Current —CMOS Inputs	$\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, f = 0, V_{CC} = 3.60V			1	4		1	30	µA

Capacitance

For all packages. Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

Notes

4. $V_{IL(min)}$ = –2.0V for pulse durations less than 20 ns.
5. $V_{IH(max)}$ = V_{CC}+0.75V for pulse durations less than 20 ns.
6. Full device AC operation assumes a 100 µs ramp time from 0 to V_{cc}(min) and 200 µs wait time after V_{cc} stabilization.
7. Only chip enable ($\overline{CE}$) and byte enables ($\overline{BHE}$ and $\overline{BLE}$) need to be tied to CMOS levels to meet the I_{SB2} / I_{CCDR} spec. Other inputs can be left floating.

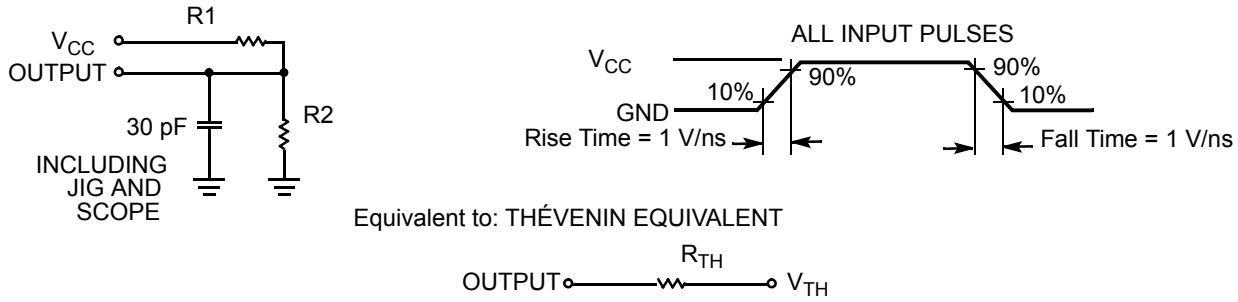
Thermal Resistance

Tested initially and after any design or process changes that may affect these parameters.

Parameter	Description	Test Conditions	VFBGA Package	TSOP II Package	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 4.25 x 1.125 inch, two-layer printed circuit board	58.85	28.2	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		17.01	3.4	°C/W

AC Test Loads and Waveforms

Figure 1. AC Test Loads and Waveforms



Parameters	2.2V - 2.7V	2.7V - 3.6V	Unit
R1	16600	1103	Ohms
R2	15400	1554	Ohms
R_{TH}	8000	645	Ohms
V_{TH}	1.2	1.75	Volts

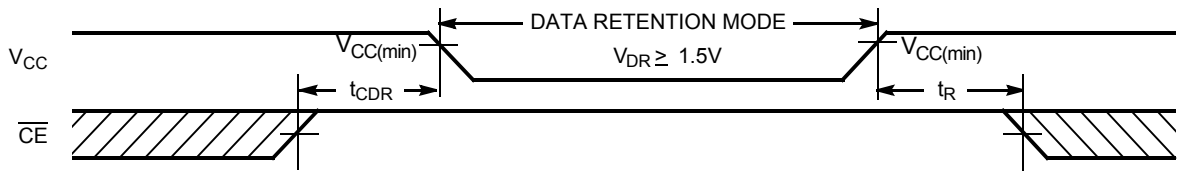
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions		Min	Typ[1]	Max	Unit
V_{DR}	V_{CC} for Data Retention			1.5			V
I_{CCDR}[7]	Data Retention Current	V_{CC}= V_{DR}, $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	Industrial			3	µA
			Automotive			30	µA
t_{CDR}[8]	Chip Deselect to Data Retention Time			0			ns
t_R[9]	Operation Recovery Time			t_{RC}			ns

Data Retention Waveform

Figure 2. Data Retention Waveform



Notes

8. Tested initially and after any design or process changes that may affect these parameters.
9. Full device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)}$ > 100 µs.

Switching Characteristics

Over the Operating Range [10, 11]

Parameter	Description	45 ns (Industrial)		55 ns (Automotive)		Unit
		Min	Max	Min	Max	
Read Cycle						
t_{RC}	Read Cycle Time	45		55		ns
t_{AA}	Address to Data Valid		45		55	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		45		55	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22		25	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z [12]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [12, 13]		18		20	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z [12]	10		10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z [12, 13]		18		20	ns
t_{PU}	$\overline{CE}$ LOW to Power Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power Down		45		55	ns
t_{DBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Data Valid		22		25	ns
t_{LZBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low Z [12]	5		5		ns
t_{HZBE}	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High Z [12, 13]		18		20	ns
Write Cycle [14]						
t_{WC}	Write Cycle Time	45		55		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	35		40		ns
t_{AW}	Address Setup to Write End	35		40		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Setup to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		40		ns
t_{BW}	$\overline{BHE}$ / $\overline{BLE}$ Pulse Width	35		40		ns
t_{SD}	Data Setup to Write End	25		25		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z [12, 13]		18		20	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z [12]	10		10		ns

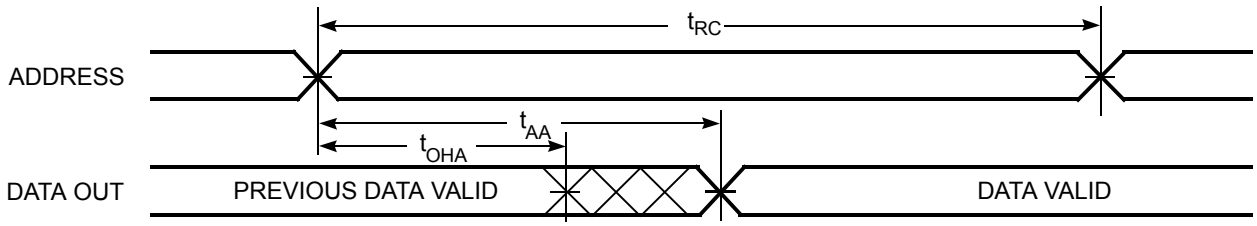
Notes

10. Test conditions assume signal transition time of 3 ns or less, timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
11. AC timing parameters are subject to byte enable signals ($\overline{BHE}$ or $\overline{BLE}$) not switching when chip is disabled. See application note AN13842 for further clarification.
12. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
13. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
14. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$ or both = V_{IL}. All signals must be active to initiate a write and any of these signals can terminate a write by going inactive. The data input setup and hold timing must refer to the edge of signal that terminates write.

Switching Waveforms

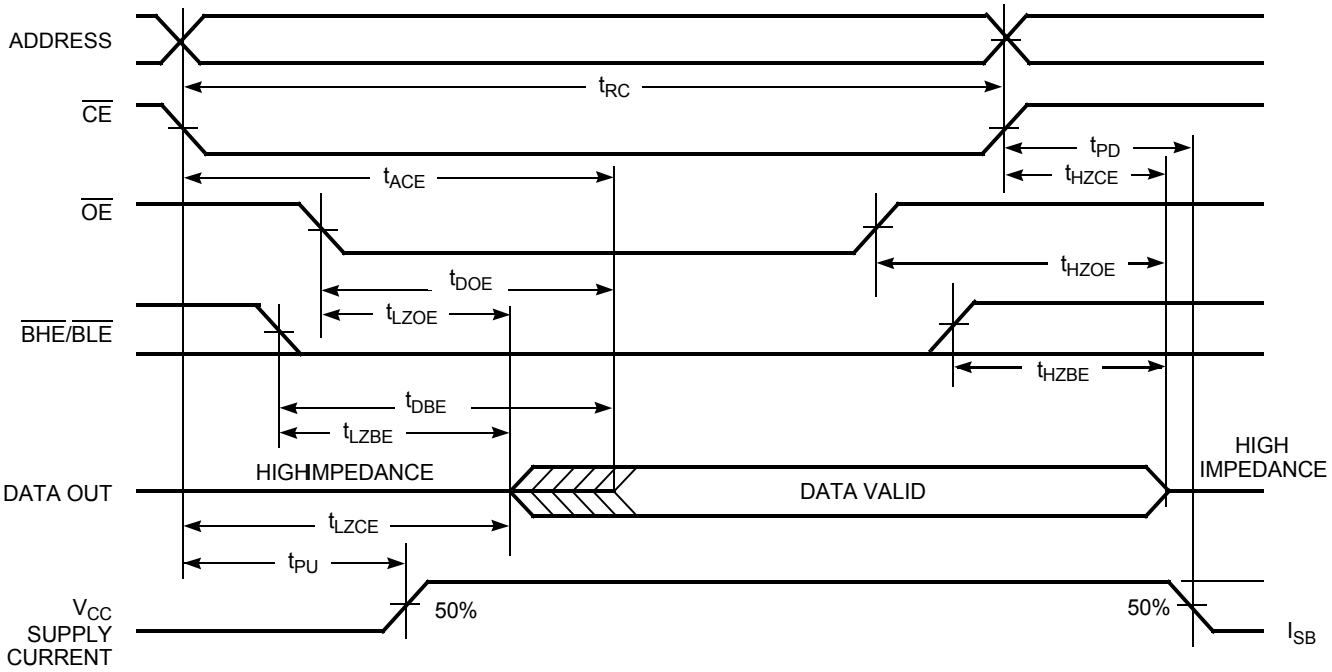
Read Cycle No. 1 (Address transition controlled)[15, 16]

Figure 3. Read Cycle No. 1



Read Cycle No. 2 ($\overline{OE}$ controlled)[16, 17]

Figure 4. Read Cycle No. 2

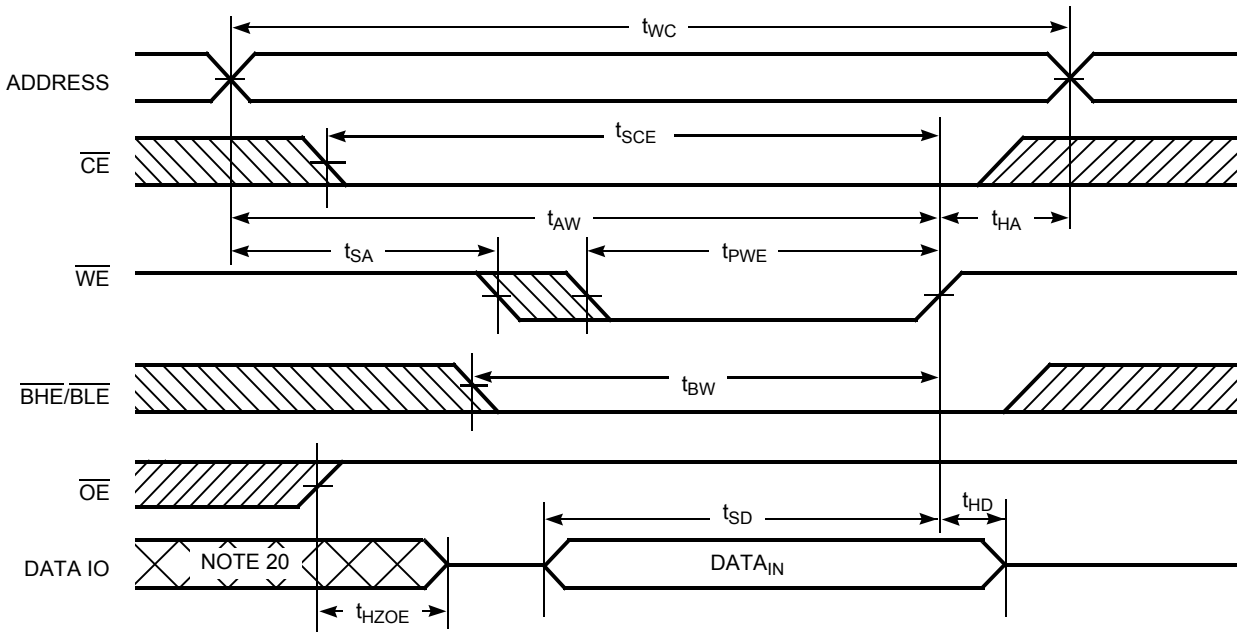


Notes
15. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}, $\overline{BHE}$, $\overline{BLE}$, or both = V_{IL}.
16. $\overline{WE}$ is HIGH for read cycle.
17. Address valid before or similar to $\overline{CE}$ and $\overline{BHE}$, $\overline{BLE}$ transition LOW.

Switching Waveforms (continued)

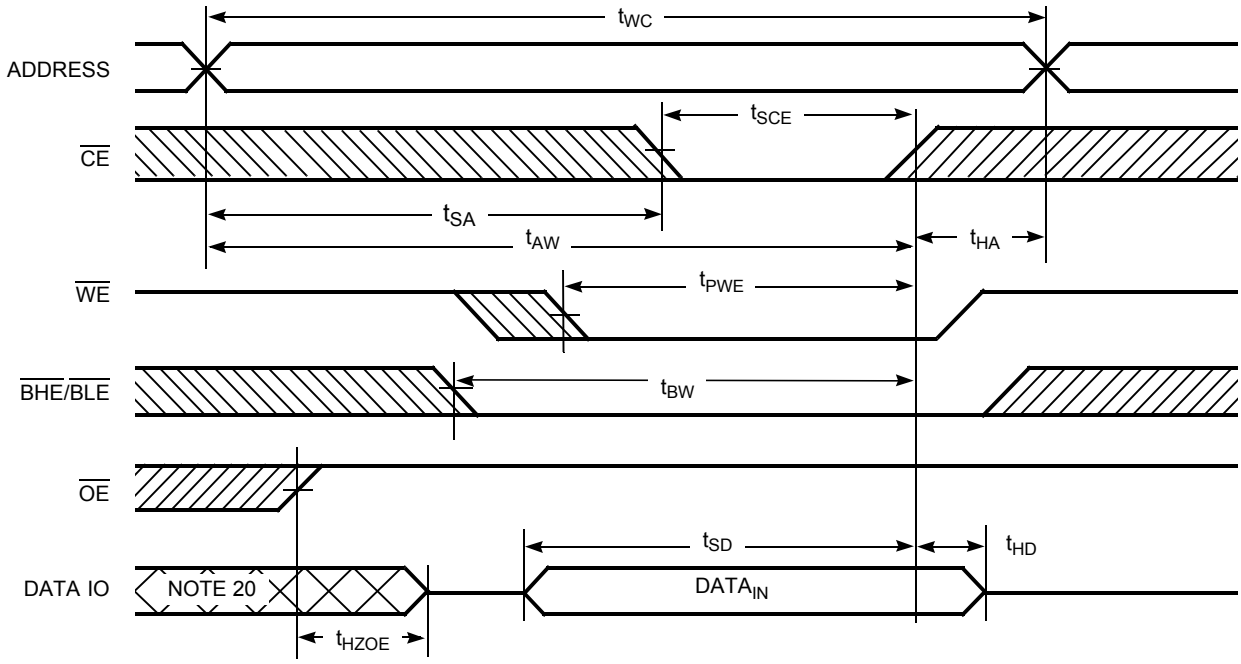
Write Cycle No. 1 ($\overline{WE}$ controlled)[14, 18, 19]

Figure 5. Write Cycle No. 1



Write Cycle No. 2 ($\overline{CE}$ controlled)[14, 18, 19]

Figure 6. Write Cycle No. 2

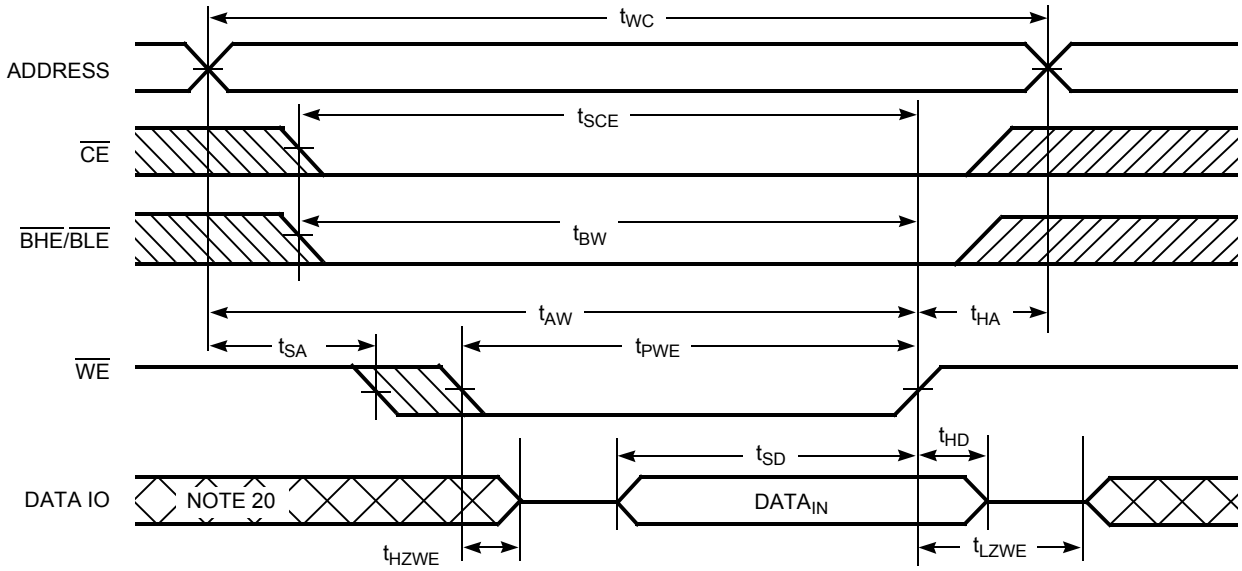


Notes
18. Data IO is high impedance if $\overline{OE}$ = V_{IH}.
19. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.
20. During this period, the IOs are in output state. Do not apply input signals.

Switching Waveforms (continued)

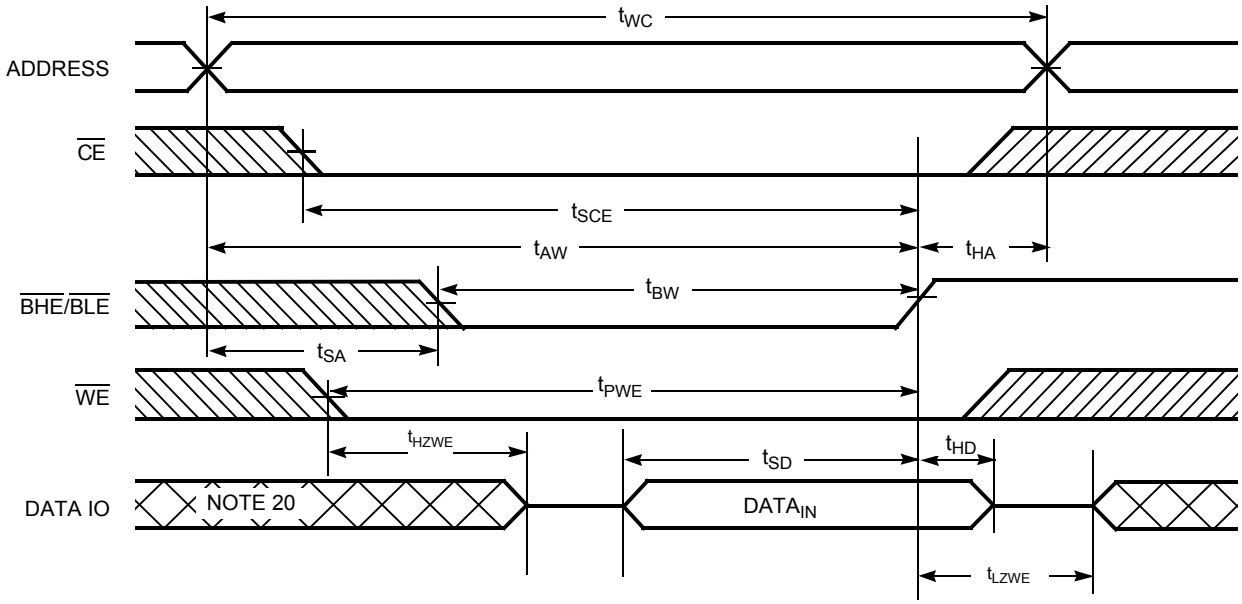
Write Cycle No. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW [19]

Figure 7. Write Cycle No. 3



Write Cycle No. 4 ($\overline{BHE/BLE}$ controlled, $\overline{OE}$ LOW)[19]

Figure 8. Write Cycle No. 4



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High Z	Deselect/Power Down	Standby (I_{SB})
X	X	X	H	H	High Z	Output Disabled	Active (I_{CC})
L	H	L	L	L	Data Out (IO_0–IO_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (IO_0–IO_7); IO_8–IO_{15} in High Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (IO_8–IO_{15}); IO_0–IO_7 in High Z	Read	Active (I_{CC})
L	H	H	L	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	H	L	High Z	Output Disabled	Active (I_{CC})
L	H	H	L	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (IO_0–IO_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (IO_0–IO_7); IO_8–IO_{15} in High Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (IO_8–IO_{15}); IO_0–IO_7 in High Z	Write	Active (I_{CC})

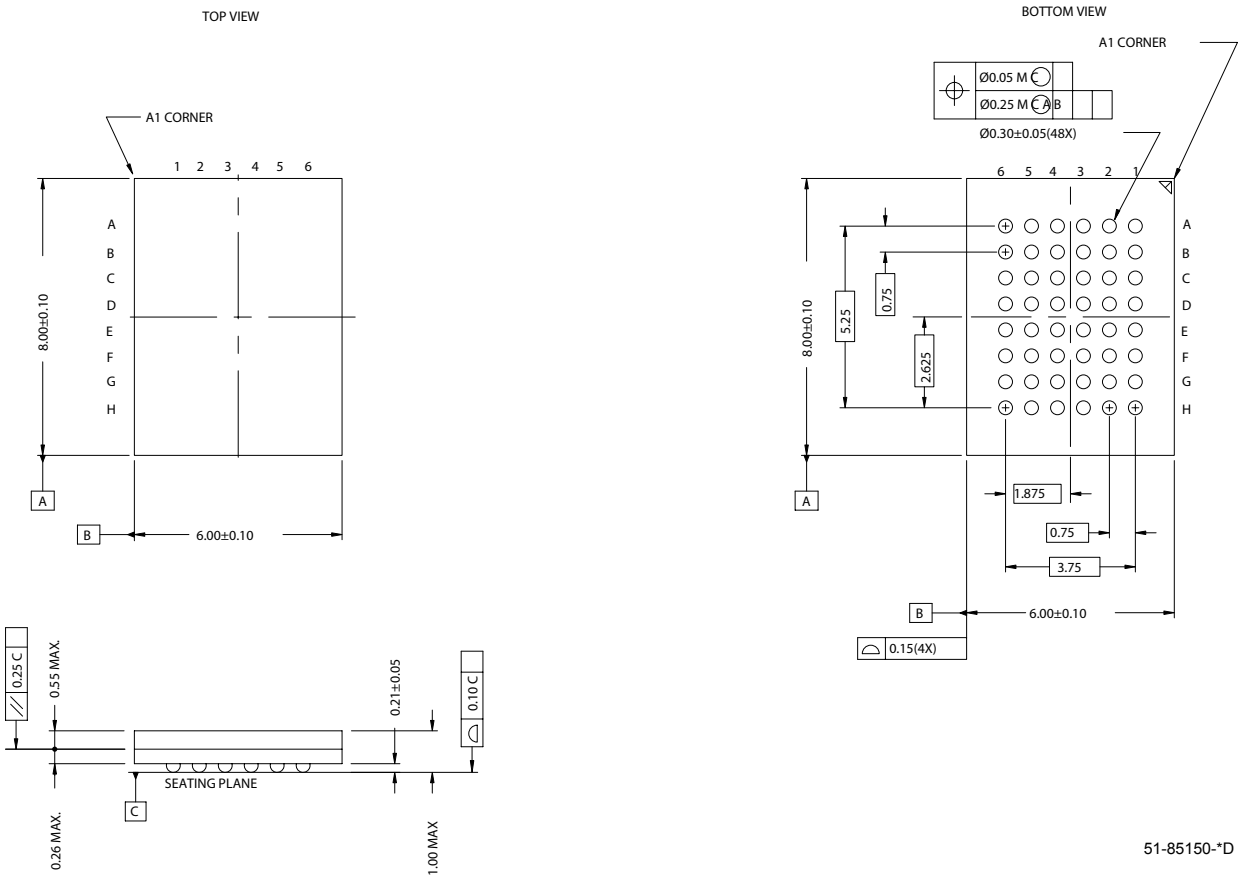
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62126EV30LL-45BVXI	51-85150	48-ball Very Fine Pitch Ball Grid Array (Pb-free)	Industrial
	CY62126EV30LL-45ZSXI	51-85087	44-pin Thin Small Outline Package II (Pb-free)	
55	CY62126EV30LL-55BVXE	51-85150	48-ball Very Fine Pitch Ball Grid Array (Pb-free)	Automotive
	CY62126EV30LL-55ZSXE	51-85087	44-pin Thin Small Outline Package II (Pb-free)	

Contact your local Cypress sales representative for availability of other parts.

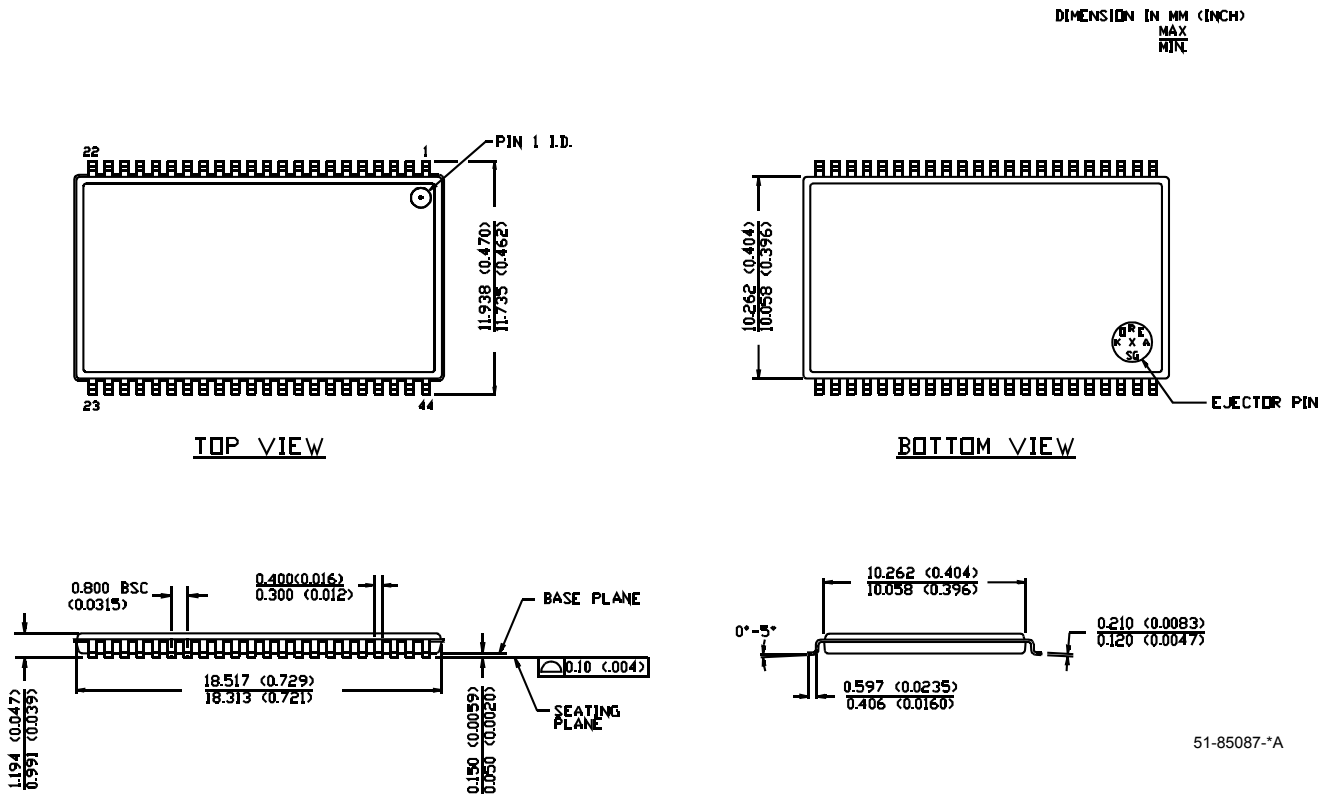
Package Diagrams

Figure 9. 48-Ball VFBGA (6 x 8 x 1 mm), 51-85150



Package Diagrams (continued)

Figure 10. 44-Pin TSOP II, 51-85087



Document History Page

Document Title: CY62126EV30 MoBL®, 1-Mbit (64K x 16) Static RAM Document Number: 38-05486				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	202760	See ECN	AJU	New data sheet
*A	300835	See ECN	SYT	Converted from Advance Information to Preliminary Specified Typical standby power in the Features Section Changed E3 ball from DNU to NC in the Pin Configuration for the FBGA Package and removed the footnote associated with it on page #2 Changed t_{OHA} from 6 ns to 10 ns for both 35- and 45-ns speed bins, respectively Changed t_{DOE}, t_{SD} from 15 to 18 ns for 35-ns speed bin Changed t_{HZOE}, t_{HZBE}, t_{HZWE} from 12 and 15 ns to 15 and 18 ns for the 35- and 45-ns speed bins, respectively Changed t_{HZCE} from 12 and 15 ns to 18 and 22 ns for the 35- and 45-ns speed bins, respectively Changed t_{SCE},t_{BW} from 25 and 40 ns to 30 and 35 ns for the 35- and 45-ns speed bins, respectively Changed t_{AW} from 25 to 30 ns and 40 to 35 ns for 35 and 45-ns speed bins respectively Changed t_{DBE} from 35 and 45 ns to 18 and 22 ns for the 35 and 45 ns speed bins respectively Removed footnote that read “$\overline{BHE}$.$\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Chip can be deselected by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$” on page # 4 Removed footnote that read “If both $\overline{BHE}$ and $\overline{BLE}$ are toggled together, then t_{LZBE} is 10 ns” on page # 5 Added Pb-free package information
*B	461631	See ECN	NXR	Converted from Preliminary to Final Removed 35 ns Speed Bin Removed “L” version of CY62126EV30 Changed $I_{CC\ (Typ)}$ from 8 mA to 11 mA and $I_{CC\ (max)}$ from 12 mA to 16 mA for f = f_{max} Changed $I_{CC\ (max)}$ from 1.5 mA to 2.0 mA for f = 1 MHz Changed I_{SB1}, $I_{SB2\ (max)}$ from 1 μA to 4 μA Changed I_{SB1}, $I_{SB2\ (Typ)}$ from 0.5 μA to 1 μA Changed $I_{CCDR\ (max)}$ from 1.5 μA to 3 μA Changed the AC Test load Capacitance value from 50 pF to 30 pF Changed t_{LZOE} from 3 to 5 ns Changed t_{LZCE} from 6 to 10 ns Changed t_{HZCE} from 22 to 18 ns Changed t_{LZBE} from 6 to 5 ns Changed t_{PWE} from 30 to 35 ns Changed t_{SD} from 22 to 25 ns Changed t_{LZWE} from 6 to 10 ns Updated the Ordering Information table.
*C	925501	See ECN	VKN	Added footnote #7 related to I_{SB2} and I_{CCDR} Added footnote #11 related AC timing parameters
*D	1045260	See ECN	VKN	Added Automotive information Updated Ordering Information table